PAP2611NS

P-Ch -20V Fast Switching MOSFET

V_{DS}=-20V, I_D=-3.4A, $R_{DS(ON)}$=60mΩ

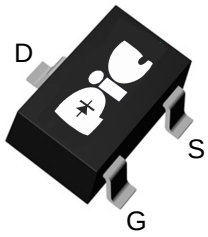
➢ General Description

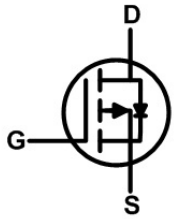
This PAP2611NS P-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent Rds(On) performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

➢ Feature

- ●Green Device Available
- ●Super Low Gate Charge
- ●Excellent CdV/dt effect decline
- ●Advanced high cell density Trench technology
- ●SOT-23S package design

➢ SOT-23S





➢ Application

- ●Load Switch
- ●Portable instrument
- ●Small power switching

➢ Absolute Maximum Ratings

Parameter	Symbol	Rating		Units
		10s	Steady State	
Drain-Source Voltage	V_{DS}	-20		V
Gate-Source Voltage	V_{GS}	±12		V
Continuous Drain Current, V_{GS} @ -4.5V[1]	I_D@T_A=25℃	-3.9	-3.4	A
Continuous Drain Current, V_{GS} @ -4.5V[1]	I_D@T_A=70℃	-3.1	-2.7	A
Pulsed Drain Current[2]	I_{DM}	-14		A
Total Power Dissipation[3]	P_D@T_A=25℃	1.32	1	W
Total Power Dissipation[3]	P_D@T_A=70℃	0.84	0.64	W
Storage Temperature Range	T_{STG}	-55 to 150		℃
Operating Junction Temperature Range	T_J	-55 to 150		℃
Thermal Resistance Junction-Ambient [1]	$R_{\theta JA}$	125		℃/W
Thermal Resistance Junction-Ambient [1] (t ≤10s)	$R_{\theta JA}$	95		℃/W
Thermal Resistance Junction-Case[1]	$R_{\theta JC}$	80		℃/W

➢ Electrical Characteristics (T_J=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V , I_D=-250uA	-20	---	---	V
BV_{DSS} Temperature Coefficient	$\triangle BV_{DSS}/\triangle T_J$	Reference to 25℃ , I_D=-1mA	---	-0.014	---	V/℃
Static Drain-Source On-Resistance[2]	$R_{DS(ON)}$	V_{GS}=-4.5V , I_D=-4A	---	50	60	mΩ
		V_{GS}=-2.5V , I_D=-3A	---	60	80	
		V_{GS}=-1.8V , I_D=-2A	---	82	100	
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}=V_{DS} , I_D =-250uA	-0.35	-0.6	-1.0	V
$V_{GS(th)}$ Temperature Coefficient	$\triangle V_{GS(th)}$		---	3.95	---	mV/℃
Drain-Source Leakage Current	I_{DSS}	V_{DS}=-16V , V_{GS}=0V , T_J=25℃	---	---	-1	uA
		V_{DS}=-16V , V_{GS}=0V , T_J=55℃	---	---	-5	
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±12V , V_{DS}=0V	---	---	±100	nA
Forward Transconductance	gfs	V_{DS}=-5V , I_D=-3A	---	12.8	---	S
Total Gate Charge (-4.5V)	Q_g	V_{DS}=-15V , V_{GS}=-4.5V , I_D=-3A	---	10.2	---	nC
Gate-Source Charge	Q_{gs}		---	1.89	---	
Gate-Drain Charge	Q_{gd}		---	3.1	---	
Turn-On Delay Time	$T_{d(on)}$	V_{DD}=-10V , V_{GS}=-4.5V , R_G=3.3Ω, I_D=-3A	---	5.6	---	ns
Rise Time	T_r		---	40.8	---	
Turn-Off Delay Time	$T_{d(off)}$		---	33.6	---	
Fall Time	T_f		---	18	---	
Input Capacitance	C_{iss}	V_{DS}=-15V , V_{GS}=0V , f=1MHz	---	857	---	pF
Output Capacitance	C_{oss}		---	114	---	
Reverse Transfer Capacitance	C_{rss}		---	108	---	

➢ Diode Characteristics

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Continuous Source Current[1,4]	I_S	V_G=V_D=0V , Force Current	---	---	-3.4	A
Pulsed Source Current[2,4]	I_{SM}		---	---	-14	A
Diode Forward Voltage[2]	V_{SD}	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1	V

Note :

1.Pulse width limited by maximum junction temperature.

2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3.Ensure that the channel temperature does not exceed 150°C.

4.The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

➢ Typical Characteristics

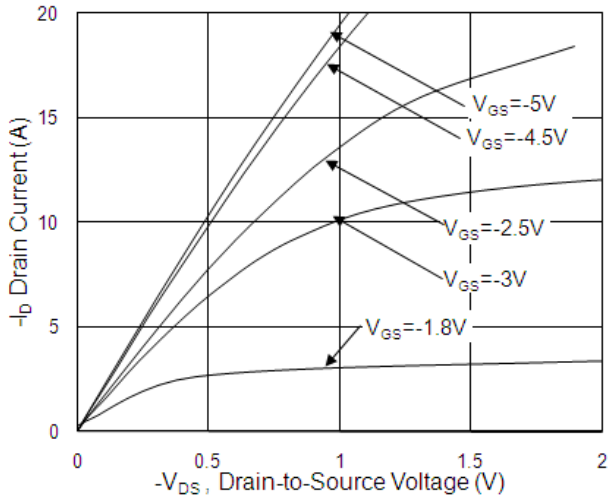


Fig.1 Typical Output Characteristics

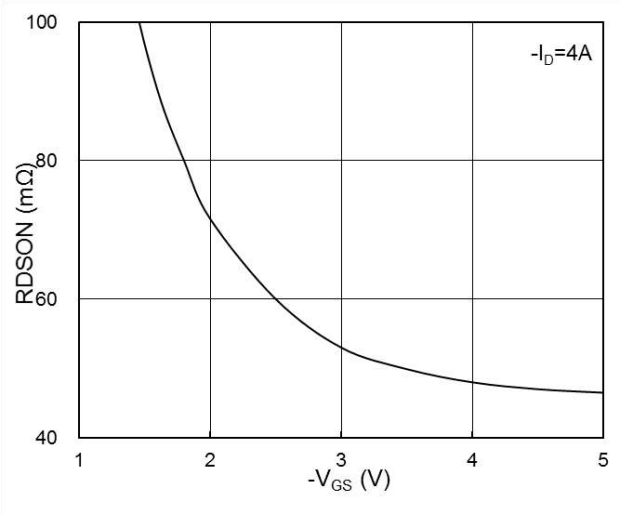


Fig.2 On-Resistance vs. G-S Voltage

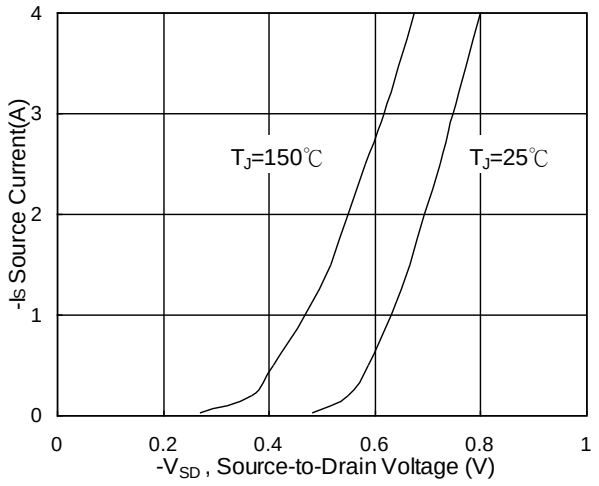


Fig.3 Forward Characteristics of Reverse

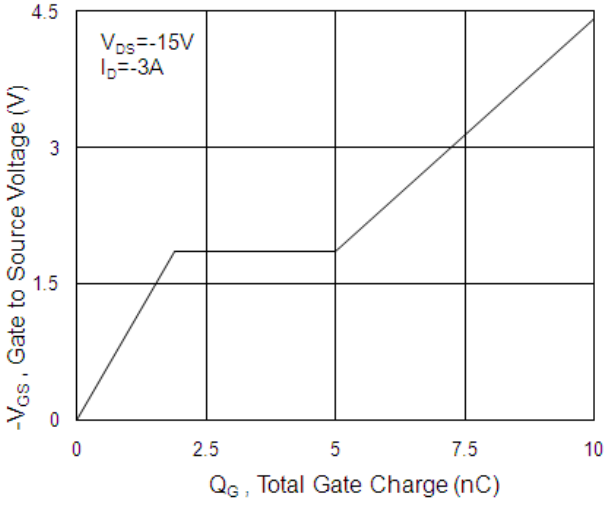


Fig.4 Gate-charge Characteristics

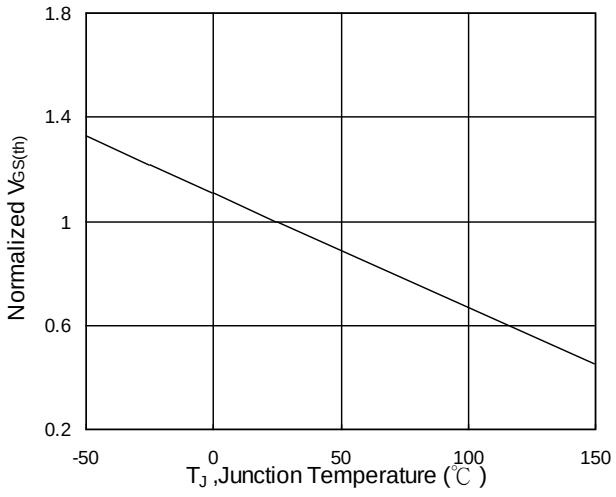


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

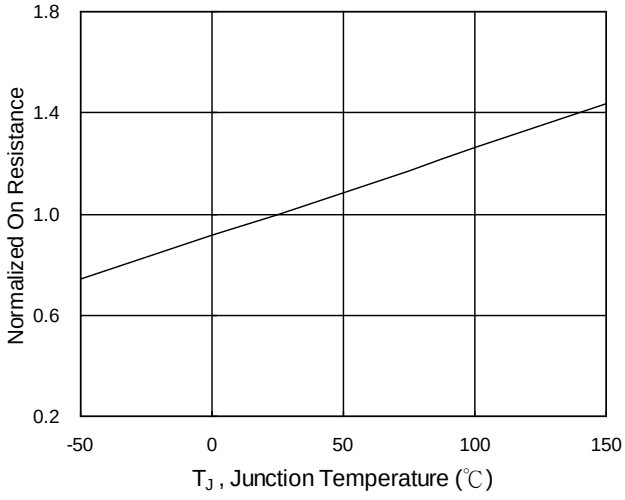


Fig.6 Normalized R_{DSON} vs. T_J

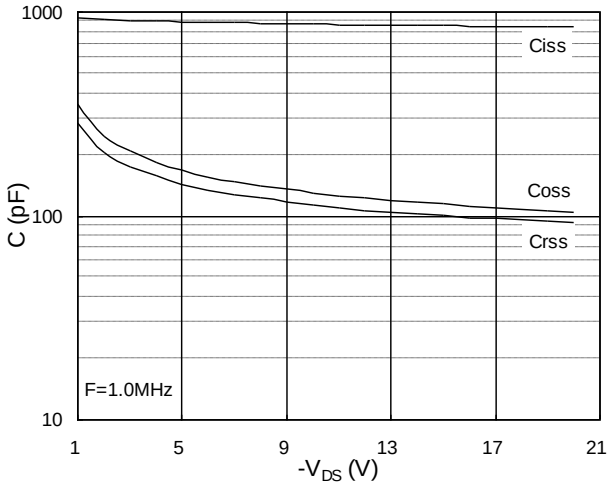


Fig.7 Capacitance

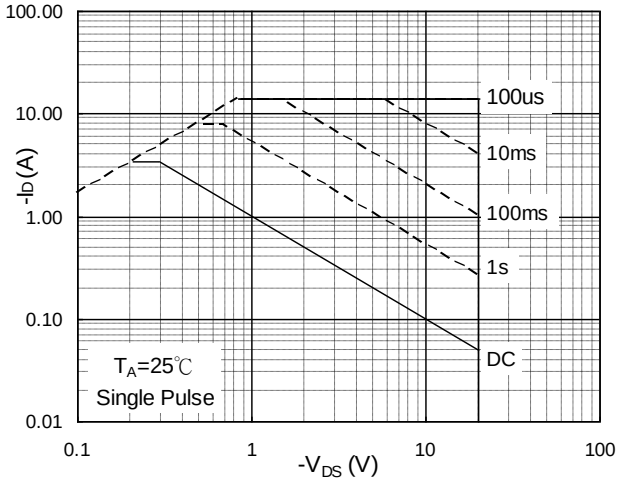


Fig.8 Safe Operating Area

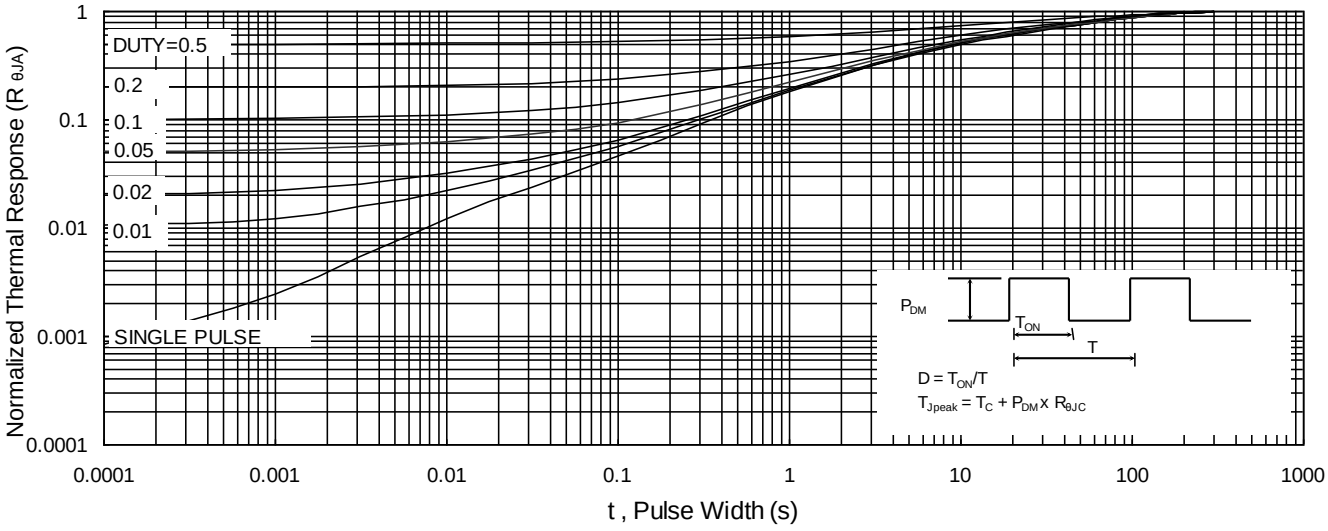


Fig.9 Normalized Maximum Transient Thermal Impedance

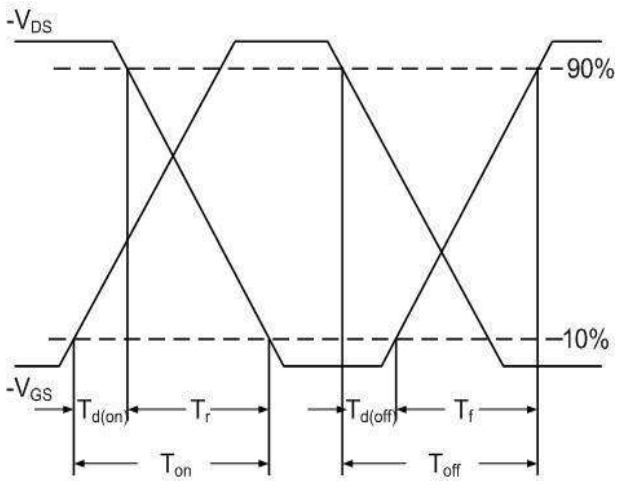


Fig.10 Switching Time Waveform

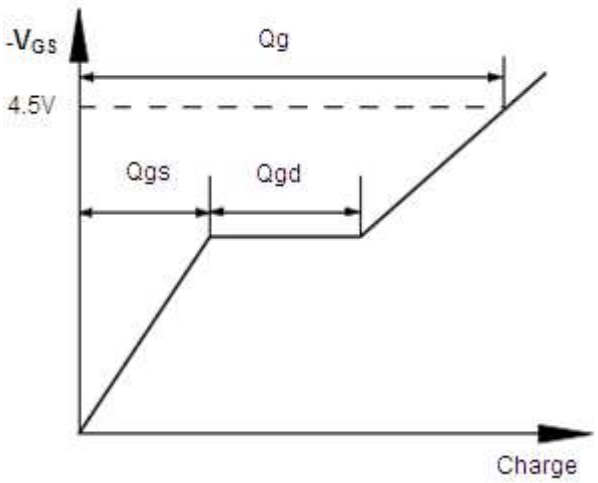
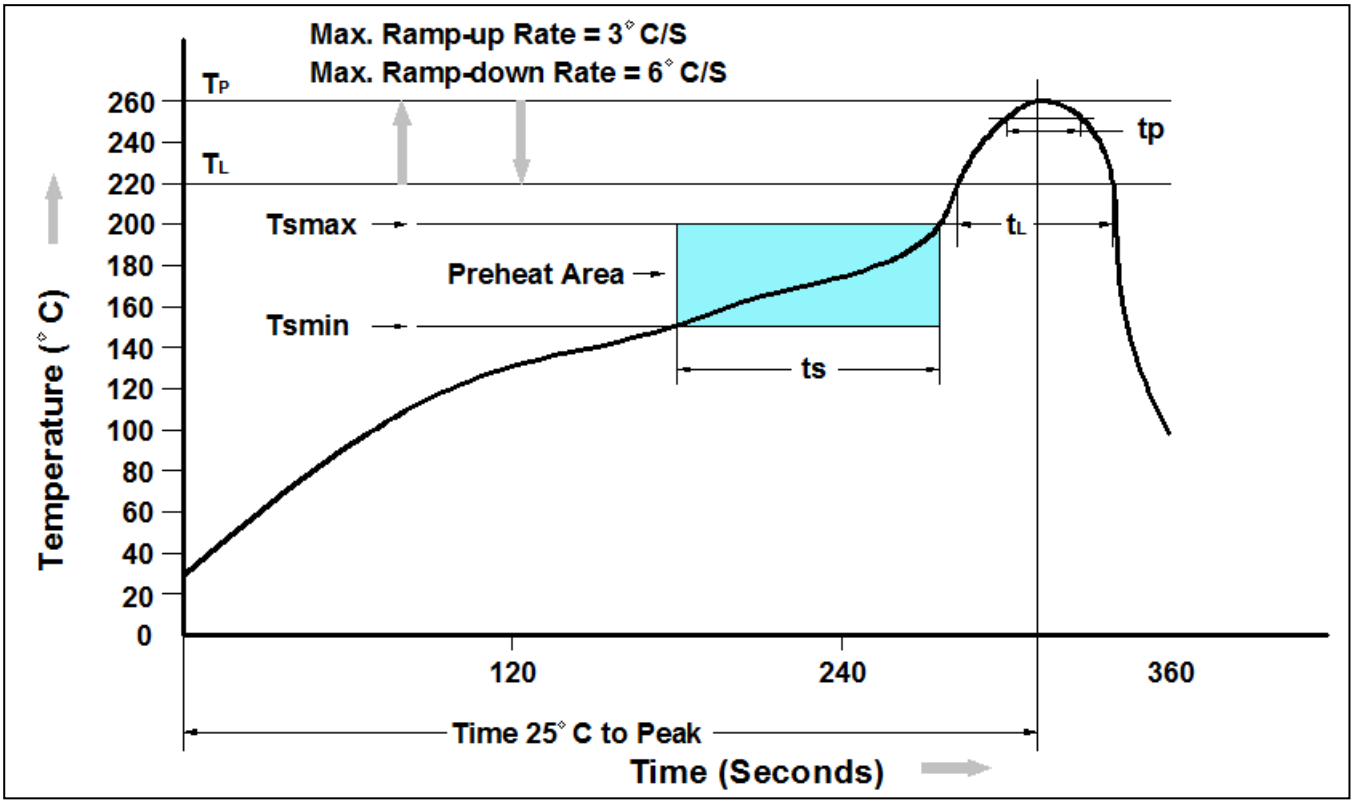


Fig.11 Gate Charge Waveform

➢ Recommand IR Reflow Soldering Thermal Profile

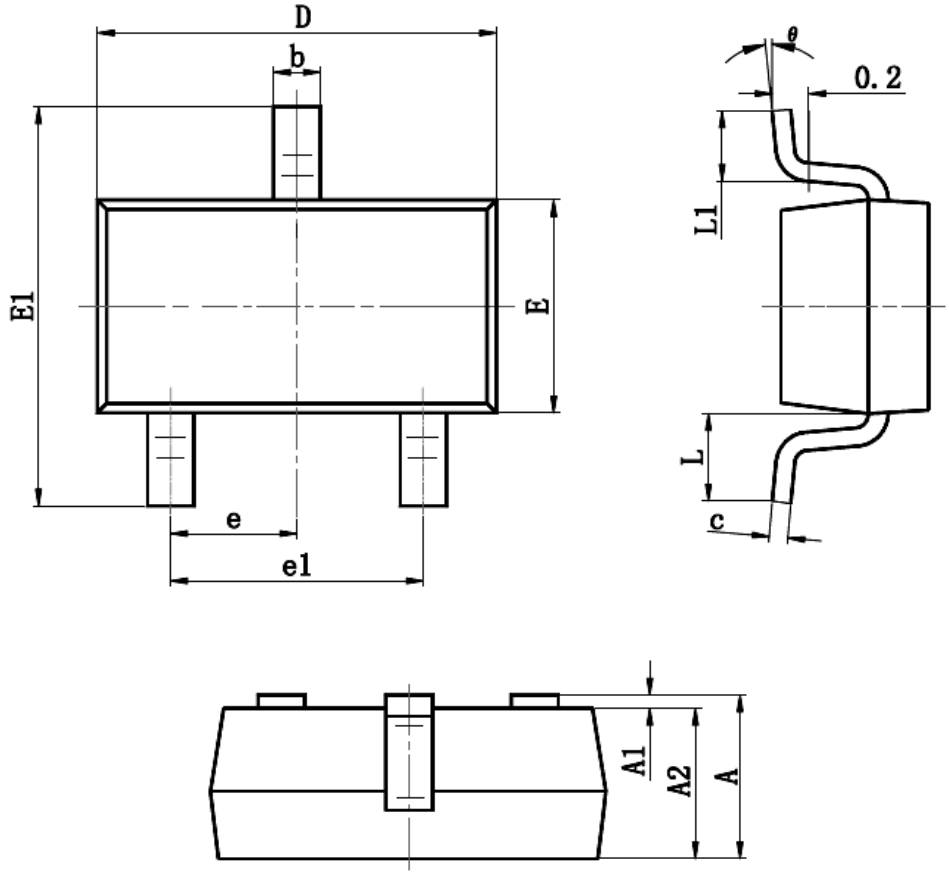


Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (ts) from (Tsmin to Tsmax)	60-120 seconds
Average Ramp-up Rate (tL to tP)	3°C/second max.
Liquidous Temperature (TL)	217°C
Time (tL) Maintained Above (TL)	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (tP) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (TP to TL)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➢ Ordering Information

Part Number	Description	Quantity
PAP2611NS	SOT-23S Reel	3000 pcs

➢ Package Information (SOT-23S)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.200	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.100	0.035	0.039
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	6°

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